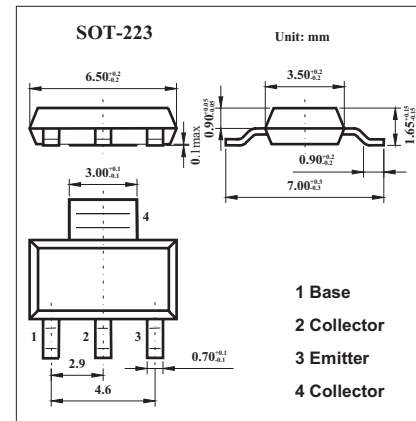


## High Voltage Transistor

## PZTA96S

## ■ Features

- PNP Silicon

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-Emmitter Voltage	$V_{CEO}$	-450	V
Collector-Base Voltage	$V_{CBO}$	-450	V
Emmitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-500	mA
Total Power Dissipation Up to $T_A = 25^\circ\text{C}$ *	$P_D$	1.5	Watts
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Thermal Resistance from Junction to Ambient *	$R_{\theta JA}$	83.3	$^\circ\text{C}$

\* Device mounted on a glass epoxy printed circuit board 1.575 in. X 1.575 in. X 0.059 in.;

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emmitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1.0\text{ mA}, I_B = 0$	-450			V
Collector-Emmitter Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\ \mu\text{A}, I_E = 0$	-450			V
Emmitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\ \mu\text{A}, I_C = 0$	-5.0			V
Collector-Base Cutoff Current	$I_{CBO}$	$V_{CB} = -400\text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Emmitter-Base Cutoff Current	$I_{EBO}$	$V_{BE} = -4.0\text{ V}, I_C = 0$			-0.1	$\mu\text{A}$
DC Current Gain*	$h_{FE}$	$I_C = -10\text{ mA}, V_{CE} = -10\text{ V}$	50		150	
Saturation Voltages	$V_{CE(sat)}$	$I_C = -20\text{ mA}, I_B = -2.0\text{ mA}$			-0.6	V
	$V_{BE(sat)}$	$I_C = -20\text{ mA}, I_B = -2.0\text{ mA}$			-1.0	V

\* Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ ; Duty Cycle = 2.0%.

## ■ Marking

Marking	ZTA96
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